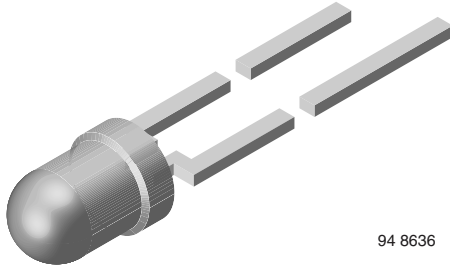


# High Power Infrared Emitting Diode, 940 nm, GaAlAs, MQW



94 8636

## DESCRIPTION

TSAL4400 is an infrared, 940 nm emitting diode in GaAlAs, MQW technology with high radiant power molded in a blue-gray plastic package.

## FEATURES

- Package type: leaded
- Package form: T-1
- Dimensions (in mm):  $\varnothing 3$
- Peak wavelength:  $\lambda_p = 940$  nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\phi = \pm 25^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Package matches with detector TEFT4300
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



## APPLICATIONS

- Infrared remote control units
- Free air transmission systems
- Infrared source for optical counters and card readers

## PRODUCT SUMMARY

COMPONENT	$I_e$ (mW/sr)	$\phi$ (deg)	$\lambda_p$ (nm)	$t_r$ (ns)
TSAL4400	36	$\pm 25$	940	15

### Note

- Test conditions see table "Basic Characteristics"

## ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSAL4400	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1
TSAL4400-RSZ	Ammopack	MOQ: 8000 pcs, 2000 pcs/box	T-1

### Note

- MOQ: minimum order quantity

## ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	5	V
Forward current		$I_F$	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu\text{s}$	$I_{FM}$	200	mA
Surge forward current	$t_p = 100 \mu\text{s}$	$I_{FSM}$	1.5	A
Power dissipation		$P_V$	160	mW
Junction temperature		$T_j$	100	$^\circ\text{C}$
Operating temperature range		$T_{amb}$	-40 to +85	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	-40 to +100	$^\circ\text{C}$
Soldering temperature	$t \leq 5$ s, 2 mm from case	$T_{sd}$	260	$^\circ\text{C}$
Thermal resistance junction / ambient	J-STD-051, leads 7 mm, soldered on PCB	$R_{thJA}$	300	K/W

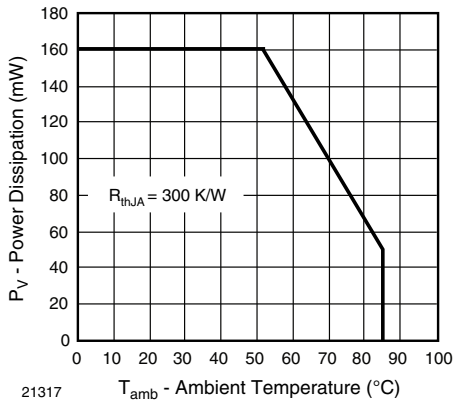


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

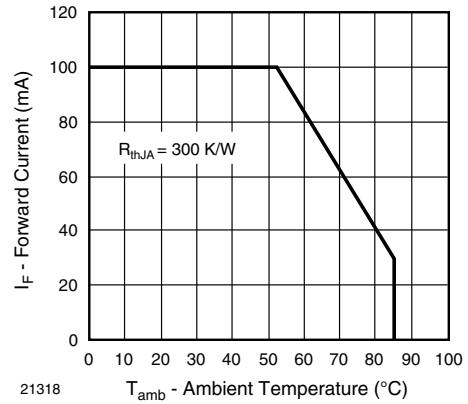


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$V_F$	-	1.35	1.6	V
	$I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$V_F$	-	2.6	3	V
Temperature coefficient of $V_F$	$I_F = 1\text{ mA}$	$TK_{V_F}$	-	-1.8	-	mV/K
Reverse current	$V_R = 5\text{ V}$	$I_R$	-	-	10	$\mu\text{A}$
Junction capacitance	$V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$	$C_j$	-	60	-	pF
Radiant intensity	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$I_e$	16	36	80	mW/sr
	$I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$I_e$	135	290	-	mW/sr
Radiant power	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$\phi_e$	-	40	-	mW
Temperature coefficient of $\phi_e$	$I_F = 20\text{ mA}$	$TK_{\phi_e}$	-	-0.6	-	%/K
Angle of half intensity		$\varphi$	-	$\pm 25$	-	deg
Peak wavelength	$I_F = 100\text{ mA}$	$\lambda_p$	-	940	-	nm
Spectral bandwidth	$I_F = 100\text{ mA}$	$\Delta\lambda$	-	25	-	nm
Temperature coefficient of $\lambda_p$	$I_F = 100\text{ mA}$	$TK_{\lambda_p}$	-	0.25	-	nm/K
Rise time	$I_F = 100\text{ mA}$	$t_r$	-	15	-	ns
Fall time	$I_F = 100\text{ mA}$	$t_f$	-	15	-	ns

**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

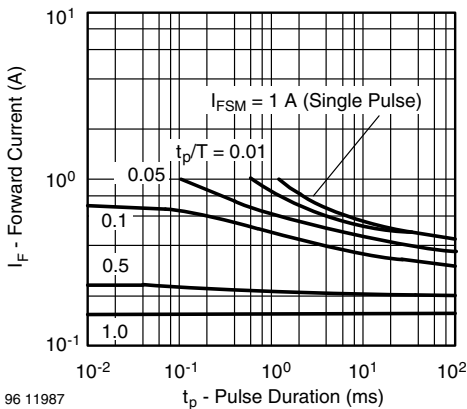


Fig. 3 - Pulse Forward Current vs. Pulse Duration

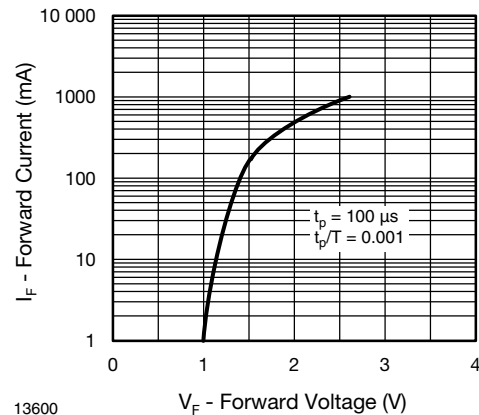


Fig. 4 - Forward Current vs. Forward Voltage

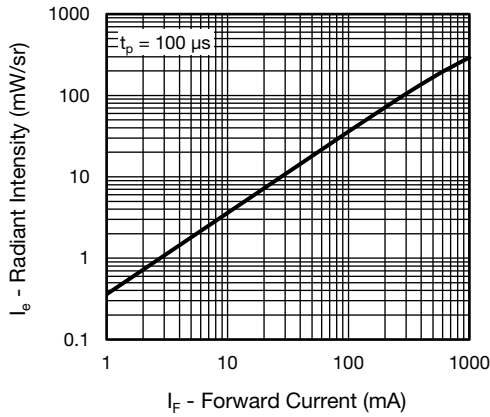


Fig. 5 - Radiant Intensity vs. Forward Current

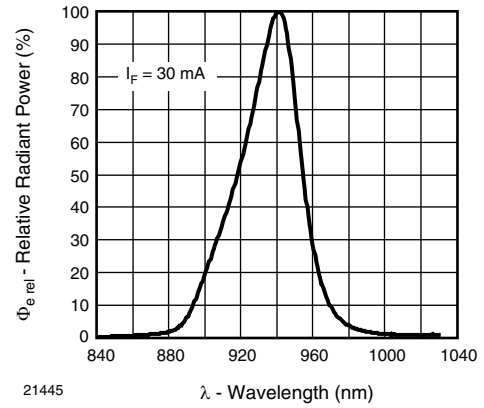


Fig. 8 - Relative Radiant Power vs. Wavelength

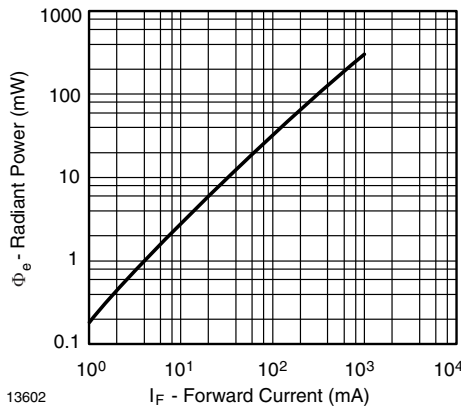


Fig. 6 - Radiant Power vs. Forward Current

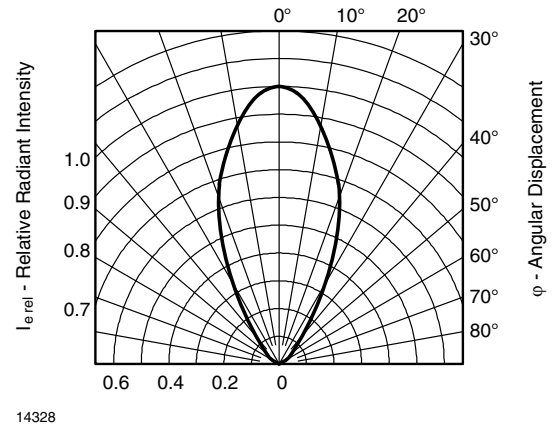


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

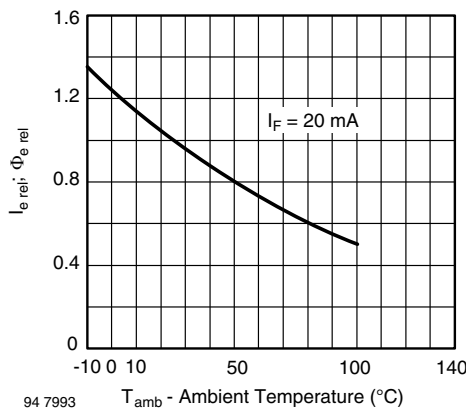
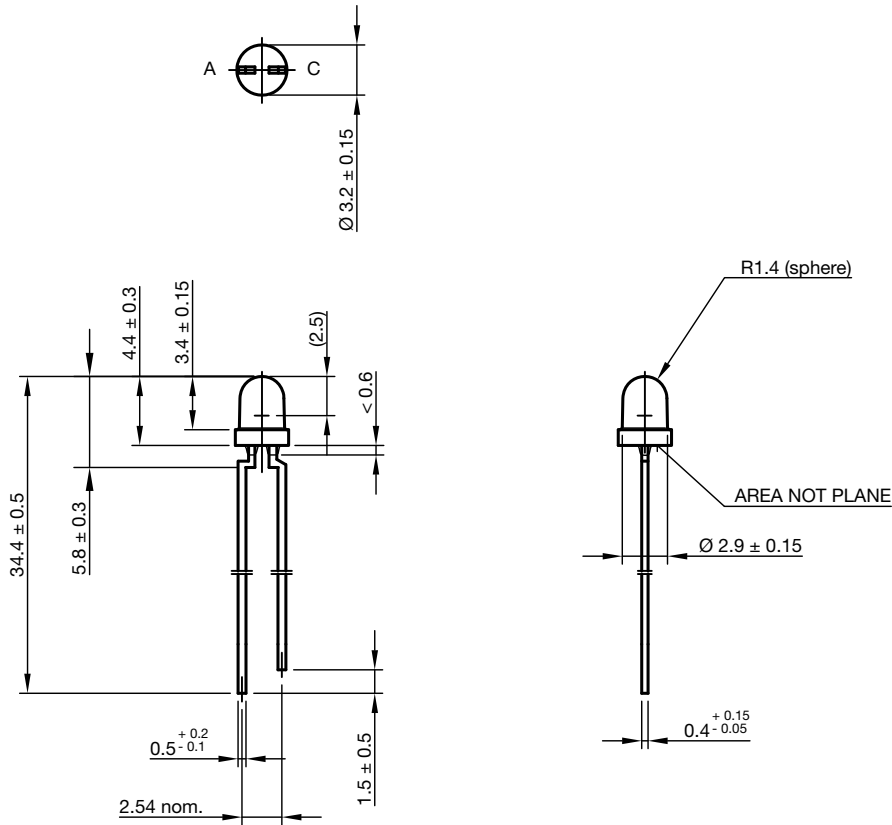
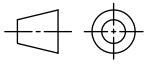


Fig. 7 - Rel. Radiant Intensity/Power vs. Ambient Temperature



**PACKAGE DIMENSIONS** in millimeters



  
technical drawings  
according to DIN  
specifications

Drawing-No.: 6.544-5255.01-4  
Issue: 9; 28.07.14



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